

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	2	("4946800").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/11/03 16:57
L3	40	("3100276" "3159780" "3209428" "3226268" "3235779" "3255055" "3317746" "3386865" "3397349" "3442011" "3457632" "3500139" "3534234" "3550292" "3586542" "3622382" "3648125" "3649386" "3663308" "3666548" "3707765" "3726719").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/03 16:58
L4	209	(atomic\$4 near smooth near surface)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/03 17:25
L5	54089	((metallurgical\$2 metal\$3) near bond\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/03 17:27
L6	0	4 same 5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/03 17:27
L7	5	4 and 5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/03 17:27
L8	690362	((solid adj state) semiconductor metal gate) near (layer film material)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/03 17:31
L9	706749	((solid adj state) semiconductor metal gate field) near (layer film material)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/03 17:31

L10	17804	9 and 5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/03 17:35
L11	52	10 and ("40" near angstrom\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/03 17:32
L12	3	("3648125" "4690714" "4946800").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/03 17:35
L13	126	9 and 4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/03 17:35
L14	12	("20020164846" "3430109" "3585714" "4371406" "4916513" "4946800" "5082793" "5696402" "6057584" "6599781").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/03 17:39
L15	14	("3354360" "3386865" "3430109" "3534234" "3586542" "3598664" "3648125" "Re28653").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/03 17:47
L16	20	("2795742" "2813048" "3100276" "3124452" "3226225" "3267405" "3430109" "3434827" "3500135" "3765956" "4136435").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/03 17:48
S1	2	("5874175").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/11/03 16:57
S2	15	("2667432" "3215555" "3901772" "3915369" "4252856" "4396677" "4608226" "4624403" "4776862" "4890783" "5161728" "5273731" "5551277").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/03/21 11:02
S3	6	("3132044" "3805372" "4348131" "4710235" "4757934").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/03/21 11:05
S4	0	("(((solidadjstate)semiconductormetalgate)n ear(layerfilmmaterial))with(nonearmorenear 40.0nearangstrom\$1)").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/03/21 13:39

S5	0	(((solid adj state) semiconductor metal gate) near (layer film material)) with (no near more near "40.0" near angstrom\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/21 13:41
S6	0	(((solid adj state) semiconductor metal gate) near (layer film material)) with ("40.0" near angstrom\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/21 13:40
S7	0	(((solid adj state) semiconductor metal gate) near (layer film material)) and (no near more near "40.0" near angstrom\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/21 13:41
S8	646122	(((solid adj state) semiconductor metal gate) near (layer film material))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/21 13:41
S9	0	((no near more) leass) near "40.0" near angstrom\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/21 13:42
S10	0	((no near more) less) near "40.0" near angstrom\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/21 13:42
S11	6	"40.0" near angstrom\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/21 13:43
S12	2356	"40" near angstrom\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/03 17:32
S13	993	S8 and S12	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/21 13:44

S14	4	S13 and (metallurgical\$2 near bond\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/03 17:26
S15	12	("20020164846" "3430109" "3585714" "4371406" "4916513" "4946800" "5082793" "5696402" "6057584" "6599781").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/03/21 13:48
S16	1	S13 and (atomic\$4 near smooth near surface)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/21 13:56
S17	1	S12 and (atomic\$4 near smooth near surface)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/03 17:25
S18	6	S12 and (metallurgical\$2 near bond\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/21 13:57
S19	18	S12 and (atomic\$4 near smooth)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/22 08:09
S20	2	("5422305" "5606177").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/03/21 14:09
S21	1	S12 and ((source drain) near pocket\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/21 14:17
S22	1632	S12 and substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/21 14:17
S23	19	S22 and (atomic\$4 near2 surface)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/21 14:22

S24	646469	(((solid adj state) semiconductor metal gate) near (layer film material))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/03 17:30
S25	2360	"40" near angstrom\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/22 08:09
S26	997	S24 and S25	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/22 08:09
S27	15	S26 and (atomic\$4 near smooth)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/22 08:10
S28	2	("6599781").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/08/08 06:48
S29	8	((("6599781") or ("6057584") or ("5696402") or ("4371406")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/11/03 12:34